General Description

The AGM16N65F combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

Application

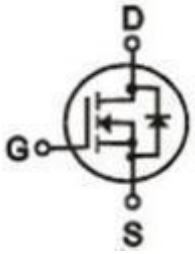
- Electronic Ballast
- Electronic Transformer
- Switch Mode Power Supply

Product Summary

BVDSS	RDSON	ID
650V	0.58Ω	16A

TO-220F Pin Configuration

TO-220F



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM16N65F	AGM16N65F	TO-220F	----	----	1000

Table 1. Absolute Maximum Ratings (Tc=25℃)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	650	V
VGS	Gate-Source Voltage (VDS=0V)	±30	V
ID	Drain Current-Continuous(Tc=25℃) **(Note 1)**	16	A
	Drain Current-Continuous(Tc=100℃)	6.4	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed **(Note 2)**	64	A
PD	Maximum Power Dissipation(Tc=25℃)	53	w
	Maximum Power Dissipation(Tc=100℃)	21	w
EAS	Avalanche energy **(Note 3)**	460	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	℃

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State)[1]	---	62.5	℃/W
RθJC	Thermal Resistance Junction-Case[1]	---	2.36	℃/W

Table 3. Electrical Characteristics (TC=25℃unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	650	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=650V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±30V,VDS=0V	--	--	±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	VDS=VGS,ID=250μA	3.0	--	4.0	V
gFS	Forward Transconductance	VDS=15V,ID=8A	--	--	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=8A	--	0.58	0.65	Ω
		VGS=4.5V, ID=8A	--	--	--	Ω
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=25V,VGS=0V, F=1MHZ	--	2063	--	pF
Coss	Output Capacitance		--	204	--	pF
Crss	Reverse Transfer Capacitance		--	29	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	--	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VDD=325V, ID=16A,RGEN=25Ω	--	54	--	nS
tr	Turn-on Rise Time		--	40	--	nS
td(off)	Turn-Off Delay Time		--	312	--	nS
tf	Turn-Off Fall Time		--	66	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=520V, ID=16A	--	74	--	nC
Qgs	Gate-Source Charge		--	10	--	nC
Qgd	Gate-Drain Charge		--	40	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)	TC=25℃	--	--	16	A
VSD	Forward on Voltage	VGS=0V,ISD=8A, TJ=25℃	--	--	1.4	V
trr	Reverse Recovery Time	Vgs=0V,IF=16A , dI/dt=100A/μs	--	682	--	ns
Qrr	Reverse Recovery Charge		--	4.5	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: T_J=25℃

Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics (T_J = 25ºC)

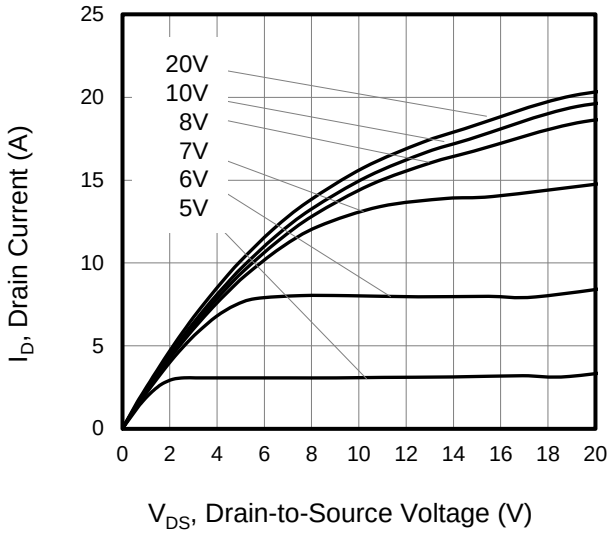


Figure 2. Body Diode Forward Voltage

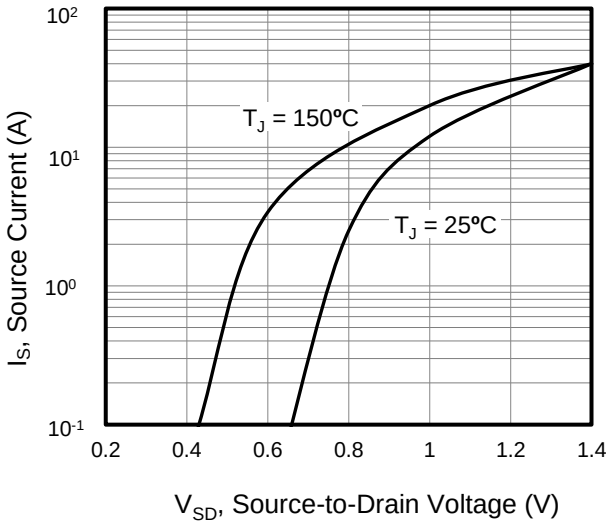


Figure 3. Drain Current vs. Temperature

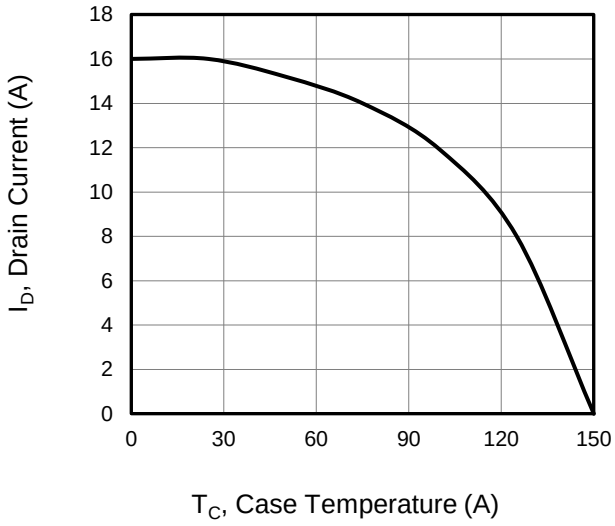


Figure 4. BV_{DSS} Variation vs. Temperature

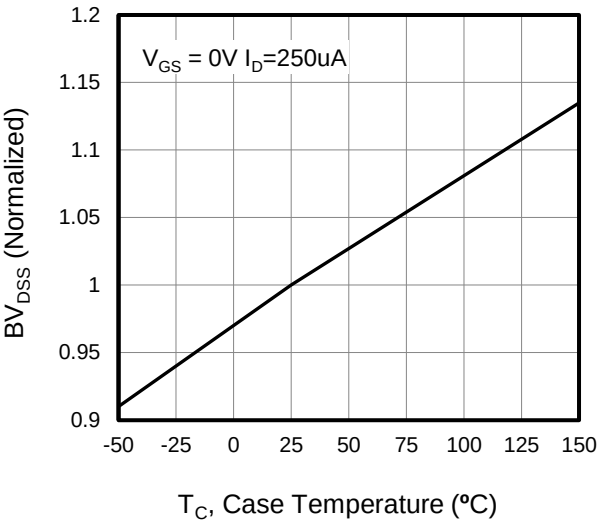


Figure 5. Transfer Characteristics

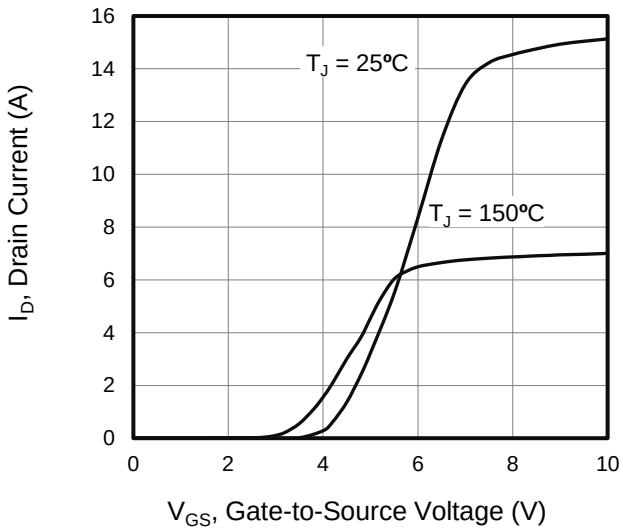
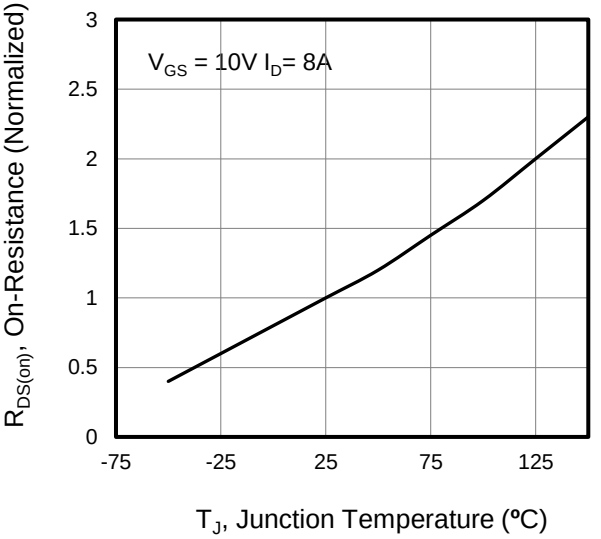


Figure 6. On-Resistance vs. Temperature



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Capacitance

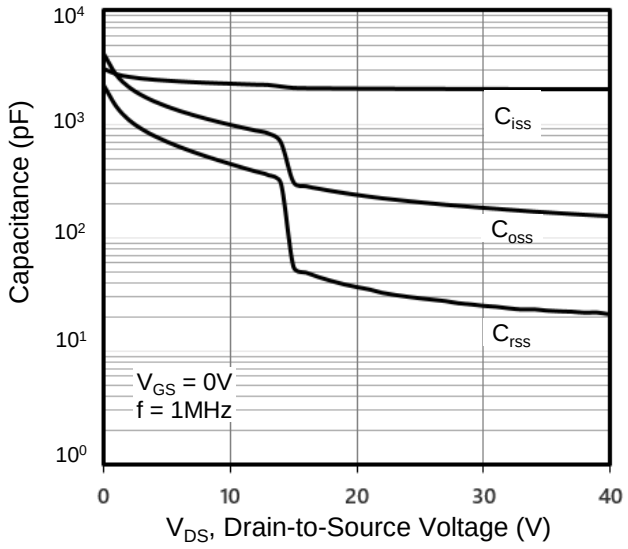


Figure 8. Gate Charge

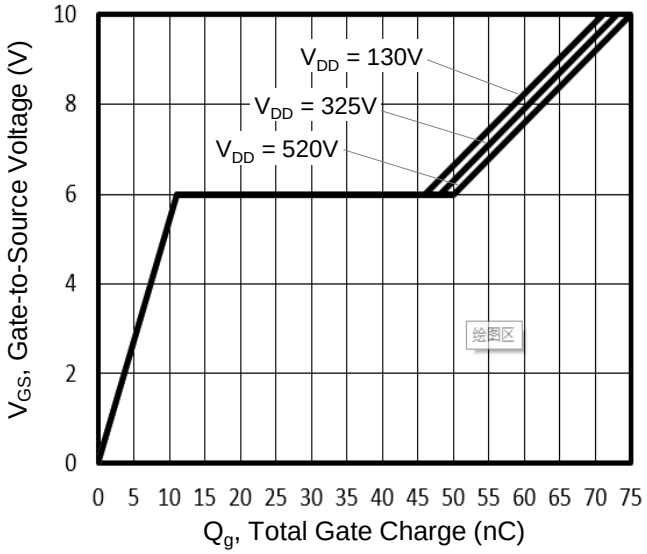


Figure 9. Transient Thermal Impedance

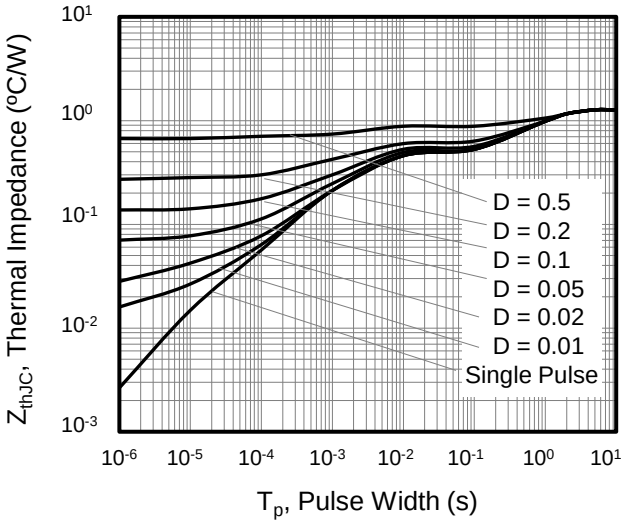


Figure A：Gate Charge Test Circuit and Waveform

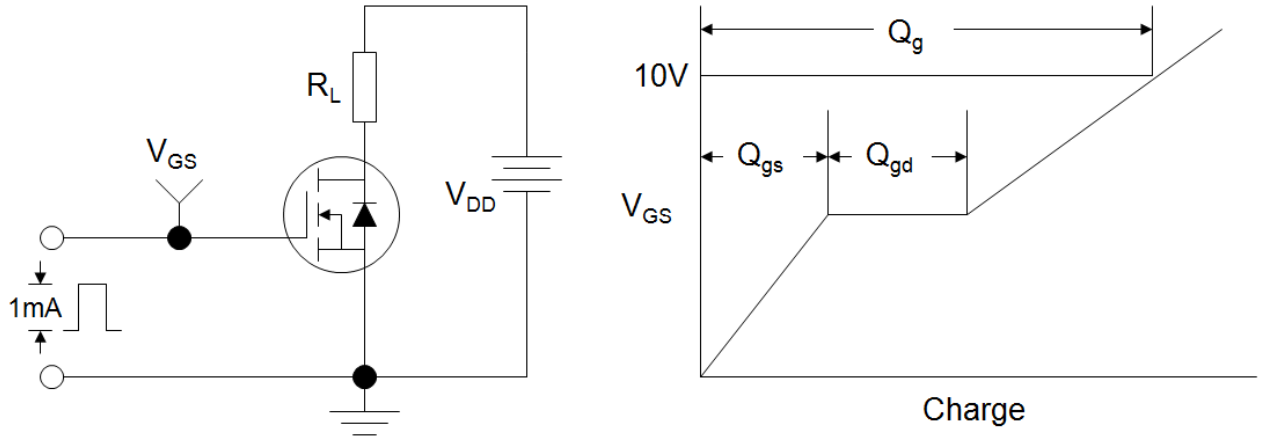


Figure B：Resistive Switching Test Circuit and Waveform

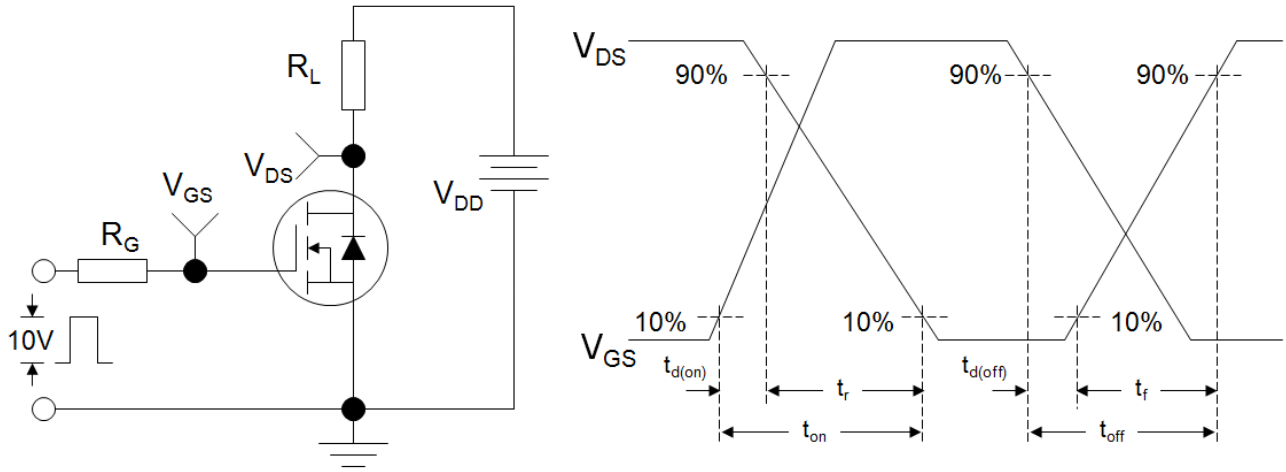
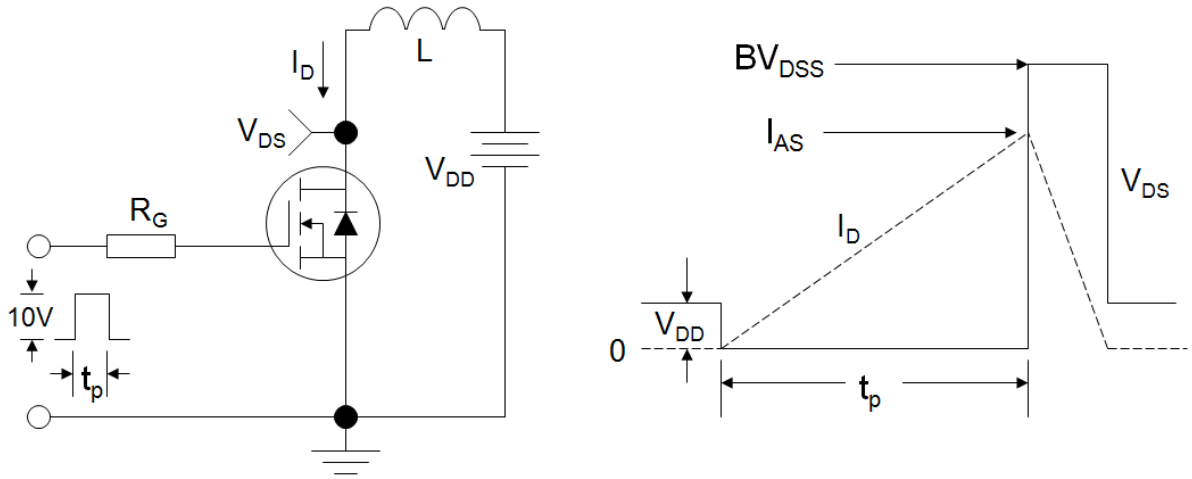
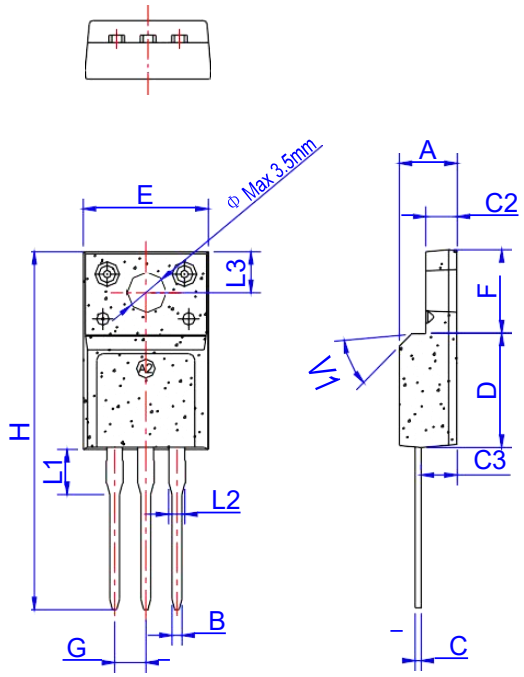


Figure C：Unclamped Inductive Switching Test Circuit and Waveform



TO-220F Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

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